

WEDNESDAY, 14 <sup>th</sup> May 2025	
8:30 – 9:00	Welcome coffee
9:00 – 9:10	OPENING SESSION
9:10 – 9:50	INVITED TALK 1 – Claire FENOUILLET-BERANGER (CEA-LETI) Chair: TBA
9:50 – 10:00	Conclusions of ICOS project – TBA
10:00 – 10:20	Coffee Break
10:20 – 12:00	SESSION 1 – “Advanced SOI materials and devices, part I” Chair: TBA
10:20 – 10:40	300 mm sSOI engineering with UltraThin BOX – David Barge (CEA-LETI)
10:40 – 11:00	Effect of PN Passivation on MOSFETs Performance in 28 nm FD-SOI – Martin Vanbrabant (UCLouvain)
11:00 – 11:20	3D simulation of charge defect impact on an industrial 28 nm FD-SOI quantum dot – Benjamin Bureau (STM)
11:20 – 11:40	Integration of W vias for individual coupling control in 28nm FD-SOI qubit arrays – Bruna Cardoso Paz (Quobly)
11:40 – 12:00	Toward Full Relaxation of sSOI Substrates for PFET Device Fabrication - Nguyet Phuong TRAN (CEA-LETI)
12:00 – 13:20	Lunch
13:20 – 14:40	SESSION 2 – “Innovative devices: simulation and compact modeling” Chair: TBA
13:20 – 13:40	Simulation of hole spin qubits in SOI quantum dots: comparison between different geometries – Lorenzo Raschi (University of Bologna)
13:40 – 14:00	Superimposed Two-contact Gate Stacks for an Improved Electrostatic Control of Si Spin Qubits – Biel Martinez i Diaz (CEA-LETI)
14:00 – 14:20	Model of Threshold Voltage and Drain Current in Core-Shell Junctionless Transistor on FD-SOI – Cunhua Dou (Nanjing University of Posts and Telecommunications)
14:20 – 14:40	Compact I-V Modeling of Short Channel MoS <sub>2</sub> FETs: A Physics-Based Approach – Ahmed Mounir (Rovira i Virgili University)
14:45 – 15:45	POSTER short presentations Chair: TBA
15:45 – 18:00	Coffee break & Poster session
19:30 – 22:00	Welcome cocktail @”W Orbicie Stońca”

THURSDAY, 15 <sup>th</sup> May 2025	
<b>9:00 – 10:40</b>	SESSION 3 – “Advanced SOI materials and devices, part II” Chair: TBA
9:00 – 9:20	Low-loss RF substrate compatible with FD-SOI integration using Si+ implantation – Martin Perrosé (CEA-LETI)
9:20 – 9:40	On the role of Power dissipation in the Post-BD Behavior of FDSOI NanoWire FETs – Rishab Goyal (Autonoma University of Barcelona)
9:40 – 10:00	Stress Enhancement and Relaxation Minimization in Locally Strained SOI with the STRASS Technique – Louis-David MOHGOUK ZOUKNAK (CEA-LETI)
10:00 – 10:20	A Schottky Barrier Field-Effect Transistor Platform with Variable Ge Content on SOI – Andreas Fuchsberger (TU Wien)
10:20 – 10:40	Electrically controlled switching of the magnetic orientation in Mn <sub>3</sub> Sn and CoFeB – B Pruckner (Christian Doppler Laboratory for Nonvolatile Magnetoresistive Memory and Logic)
<b>10:40 – 11:00</b>	Coffee break
<b>11:00 – 12:40</b>	SESSION 4 – “New channel materials for CMOS electronics” Chair: TBA
11:00 – 11:40	INVITED TALK 2 – Xinran Wang (Nanjing University)
11:40 – 12:00	Plasma-Enhanced ALD Growth of 2D Devices on SiO <sub>2</sub> /Si Wafer Substrates – Carlos Marquez (University of Granada)
12:00 – 12:20	Design guidelines for Gr-MoS <sub>2</sub> based DS-FETs – Tommaso Ugolini (University of Bologna)
12:20 – 12:40	ITO Interconnects for Transparent Electronics – Doga Selin Memikoglu (KTH)
<b>12:40 – 14:00</b>	Lunch
<b>14:00 – 15:40</b>	SESSION 5 – “Memory devices and structures” Chair: TBA
14:00 – 14:40	INVITED TALK 3 – Minsoo Yoo (SK Hynix Inc.)
14:40 – 15:00	Nor-type Gated Diode Synapse Array with Selective Program/Erase Operation Capabilities – Kyu-Ho Lee (Seoul National University)
15:00 – 15:20	Analog Resistive Switching Phenomena in Titanium Oxide Thin-Film Memristive Devices – Karimul Islam (WUT)
15:20 – 15:40	A Closed-Form Model for Programming of Oxide-Based Resistive Random Access Memory Cells Derived From the Stanford Model – Nadine Dersch (THM University of Applied Sciences)
<b>15:40 – 16:00</b>	Coffee break

<b>16:00 – 17:00</b>	<p style="text-align: center;">SESSION 6 – “Biosensors”</p> <p style="text-align: center;">Chair: TBA</p>
16:00 – 16:20	Silicon Nanowire Field-Effect Transistor Biosensors with Bowtie Antenna – Svetlana Vitusevich (Forschungszentrum Juelich)
16:20 – 16:40	Influence of Gate Capacitance Ratio on ISFET Memory – Henrique Lanfredi Carvalho (University of Sao Paulo)
16:40 – 17:00	Graphene-enabled glucose sensing: From field-effect transistors to next-generation wearables – Vicente Silva Lopes (INL)
<b>19:00 – 23:00</b>	Excursion + Gala dinner @Bazyliszek, “The Old Town”

FRIDAY, 16 <sup>th</sup> May 2025	
<b>9:00 – 10:40</b>	SESSION 7 – “Device simulation, characterization, and compact modeling, part I” Chair: TBA
9:00 – 9:20	Geometrical Variability Impact on the Gate Tunneling Leakage Mechanisms in FinFETs – Cristina Medina-Bailon (University of Granada)
9:20 – 9:40	Coverage Ratio of Bottom Channel on Intrinsic Device Characteristics of GAA Si NS CFETs – Sekhar Reddy Kola (National Yang Ming Chiao Tung University)
9:40 – 10:00	Band Structure-based Estimation of Radiation Tolerance and Reliability of UTB MOS Devices – Nalin Vilochan Mishra (Indian Institute of Science Education and Research)
10:00 – 10:20	MULHACEN, enhanced multi-subband Monte Carlo simulator for non-planar FETs – Luca Donetti (University of Granada)
10:20 – 10:40	DC Parameter Analysis of Asymmetric VNW JL GAA pMOSFETs on SOI from 300K to 400K – Abderrahim TAHIAT (ENSICAEN)
<b>10:40 – 11:00</b>	Coffee break
<b>11:00 – 12:40</b>	SESSION 8 – “Device simulation, characterization, and compact modeling, part II” Chair: TBA
11:00 – 11:40	<b>INVITED TALK 4 – Mikael Ostling (KTH)</b>
11:40 – 12:00	Statistical Enhancement in Two-particle Device Monte Carlo – Josef Gull (Institute for Microelectronics)
12:00 – 12:20	Monte Carlo analysis of hot electron injection in the passivation layer above GaN HEMTs – Pierpaolo Palestri (University of Modena)
12:20 – 12:40	A Methodology for PDK Re-Centering Using TCAD and Experimental Data for Cryogenic Temperatures – Tapas Dutta (Semiwise Ltd.)
<b>12:40 – 13:20</b>	Lunch
<b>13:20 – 14:40</b>	SESSION 9 – “Alternative transistors architectures and variability” Chair: TBA
13:20 – 13:40	Experimental Investigation of 7-Level Stacked Nanosheet nMOSFETs for High-Temperature Applications – Michelly de Souza (Centro Universitário FEI)
13:40 – 14:00	Application of Forksheet Transistor in Operational Transconductance Amplifier – Joao Martino (University of Sao Paulo)
14:00 – 14:20	Assessing the Impact of Process and Design Variations on Reliability of Complementary FET – Ankit Dixit (University of Glasgow)
14:20 – 14:40	Fracture dynamics in Smart Cut technology: Wafer deformation measurement – Lucas Colonel (CEA-LETI)
14:40 – 15:00	Conference closing and coffee break